

T2800D





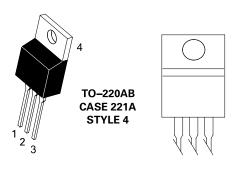
Description

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

Features

- Blocking Voltage to 400 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Four Quadrant Gating
- Pb–Free Package is Available

Pin Out



Functional Diagram



Additional Information





Samples

Thyristors Surface Mount – 400V > T2800D

Maximum Ratings (T₁ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) $(T_J = -40 \text{ to } +125^{\circ}\text{C}, \text{ Gate Open})$	V _{DRM} , V _{RRM}	400	V
On-State RMS Current (All Conduction Angles, T _c = +80°C)	I _{T (RMS)}	8.0	А
Peak Non–Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, $T_J = +80^{\circ}$ C)	I _{TSM}	100	А
Circuit Fusing Considerations (t = 8.3 ms)	l²t	40	A2s
Peak Gate Power (Pulse Width = 10 μ sec, $T_c = +80$ °C)	P_{GM}	16	W
Average Gate Power (t = 8.3 msec, $T_c = +80^{\circ}$ C)	P _{GM (AV)}	0.35	W
Peak Gate Current (Pulse Width = 10 µsec, T _C = +80°C)	I _{GM}	4.0	А
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R _{euc}	2.2	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Sec	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Electrical Characteristics - **OFF** ($T_J = 25^{\circ}$ C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T ₁ = 25°C	I _{DRM} ,	-	-	0.01	m ^
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_{J} = 100^{\circ}C$	I	-	-	2.0	mA

Electrical Characteristics - ON (T_{.i} = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Forward On-State Voltage (Note 2) $(I_{TM} = \pm 30 \text{ A})$		V _{TM}	-	1.7	2.0	V
	MT2(+), G(+)		_	10	25	
Gate Trigger Current (Continuous dc)	MT2(+), G(-)		_	20	60	, ma A
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)	GT	_	15	25	mA mA
	MT2(-), G(+)		_	30	60	
Gate Trigger Voltage (Continuous dc) (All Four Quadrants) (V $_{D}$ = 12 Vdc, R $_{L}$ = 100 $\Omega)$		V _{GT}	_	1.25	2.5	V
Gate Non–Trigger Voltage (Continuous dc) $(V_D = 12 \text{ Vdc}, R_L = 100 \Omega, T_C = 100^{\circ}\text{C})$		$V_{\rm GD}$	0.2	_	_	V
Holding Current $(V_D = 12 \text{ Vdc, Gate Open , Initiating Current}) = \pm 200 \text{ mA})$		I _H	-	15	30	mA
Gate Controlled Turn-On Time (V_D = Rated $V_{DRM'}$ I_T = 10 A , I_{GT} = 80 mA, Rise Time = 0.1 μ s)		t _{gt}	_	1.6	_	μs

^{1.} V_{DRM} and V_{BRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



Dynamic Characteristics

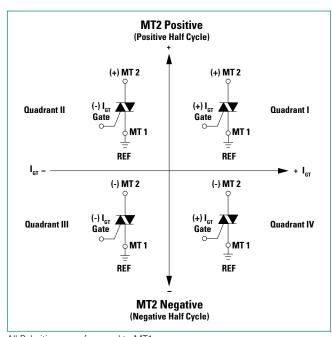
Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate-of-Rise of Commutation Voltage (V_D = Rated V_{DRM} , $I_{T(RMS)}$ = 8 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, T_C = 80°C)	dv/dt _(c)	_	10	_	V/µs
Critical Rate-of-Rise of Off-State Voltage $(V_D = Rated V_{DRM'} Exponential Voltage Rise, Gate Open, T_C = 100°C)$	dv/dt	60	-	_	V/µs

^{2.} Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
IRRM	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All Polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used

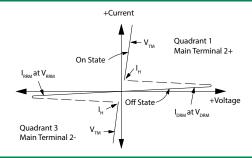


Figure 1. Current Derating

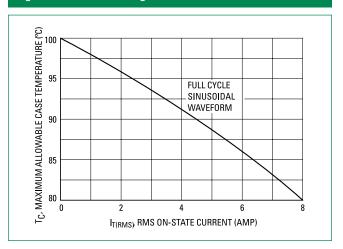
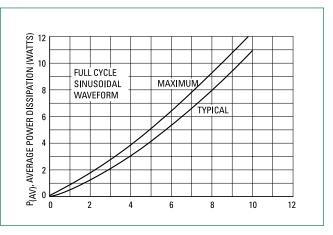
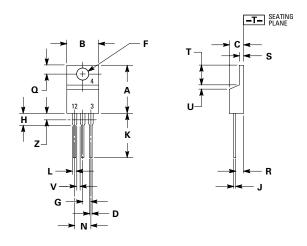


Figure 2. Power Dissipation

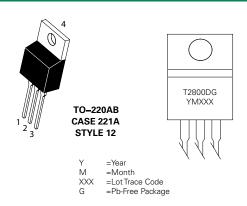




Dimensions



Part Marking System



Dim	Inc	ches Millimo		neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z	_	0.080		2.04

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

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Device	Package	Shipping
T2800D	TO-220AB	
T2800DG	TO-220AB (Pb-Free)	1000 Units/ Box

2. CONTROLLING DIMENSION: INCH.

^{1.} DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.